



Solid State Devices, Inc.

14701 Firestone Blvd. * La Mirada, Ca 90638
Phone: (562) 404-4474 * Fax: (562) 404-1773
ssdi@ssdi-power.com * www.ssdi-power.com

SED15HB100 SED15HE100

Designer's Data Sheet

Part Number / Ordering Information ^{1/}

SED15 _ 100 _

L Screening^{2/} = None
TX = TX Level
TXV = TXV Level
S = S Level

L Configuration

HB = without lead
HE = with lead

**15 AMP
100 VOLTS
SCHOTTKY RECTIFIER**

FEATURES:

- Low Reverse Leakage
- Low Forward Voltage Drop
- Hermetically Sealed Power Surface Mount Package
- Guard Ring for Overvoltage Protection
- Eutectic Die Attach
- 175°C Operating Temperature
- TX, TXV, and Space Level Screening Available^{2/}

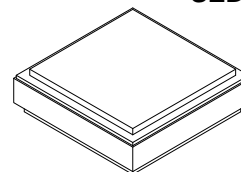
MAXIMUM RATINGS		Symbol	Value	Units
Peak Repetitive Reverse Voltage and DC Blocking Voltage		V_{RRM} V_{RWM} V_R	100	Volts
Average Rectified Forward Current (Resistive Load, 60 Hz, Sine Wave, $T_A = 100^\circ\text{C}$)		I_O	15	Amps
Peak Surge Current (8.3 ms Pulse, Half Sine Wave Superimposed on I_O , allow junction to reach equilibrium between pulses, $T_A = 25^\circ\text{C}$)		I_{FSM}	175	Amps
Operating and Storage Temperature		$T_{OP} \& T_{stg}$	-55 to +175	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case		$R_{\theta JC}$	1.3	$^\circ\text{C/W}$

Notes:

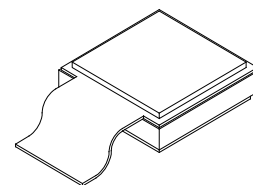
1/ For ordering information, price, operating curves, and availability – Contact factory.

2/ Screening based on MIL-PRF-19500. Screening flows available on request.

SEDPACK 1



HB Series



HE Series

NOTE: All specifications are subject to change without notification.
SCD's for these devices should be reviewed by SSDI prior to release.

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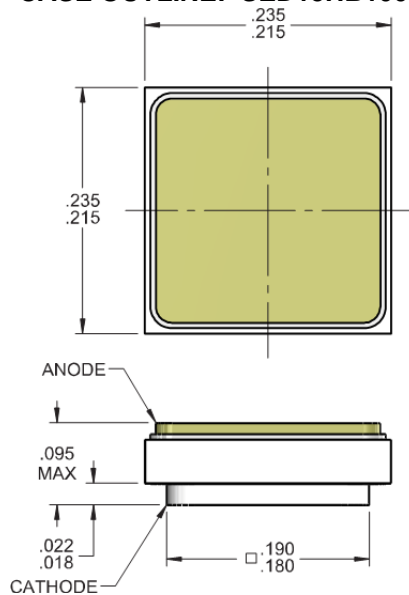
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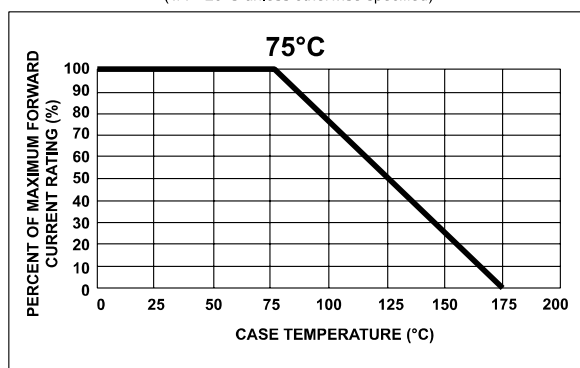
SED15HB100 SED15HE100

ELECTRICAL CHARACTERISTICS	Symbol	Maximum	Unit
Instantaneous Forward Voltage Drop ($I_F = 10 A_{DC}$, $T_A = 25^\circ C$, 300 μsec Pulse) ($I_F = 15 A_{DC}$, $T_A = 25^\circ C$, 300 μsec Pulse)	V_{F1} V_{F2}	0.78 0.83	V_{DC}
Instantaneous Forward Voltage Drop ($I_F = 10 A_{DC}$, $T_A = +125^\circ C$, 300 μsec Pulse) ($I_F = 15 A_{DC}$, $T_A = +125^\circ C$, 300 μsec Pulse)	V_{F3} V_{F4}	0.63 0.67	V_{DC}
Reverse Leakage Current (Rated V_R , $T_A = 25^\circ C$, 300 μsec pulse minimum)	I_{R1}	1.5	mA
Reverse Leakage Current (Rated V_R , $T_A = 100^\circ C$, 300 μsec pulse minimum)	I_{R2}	10	mA
Junction Capacitance ($V_R = 10V$, $T_A = 25^\circ C$, $f = 1 MHz$)	C_J	600	pF

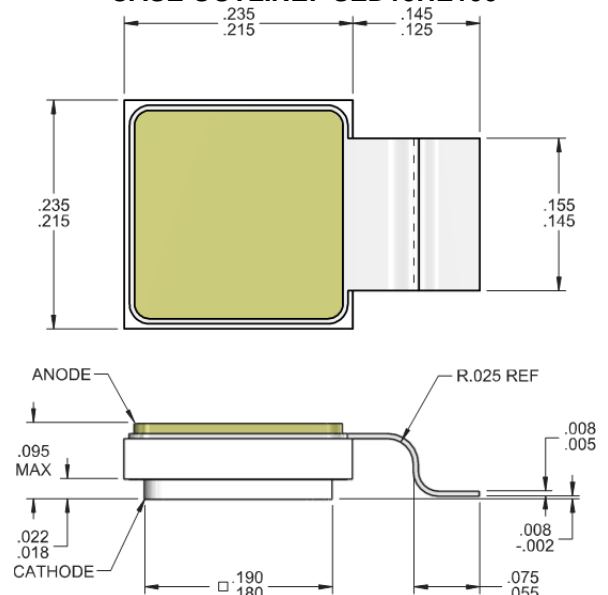
CASE OUTLINE: SED15HB100



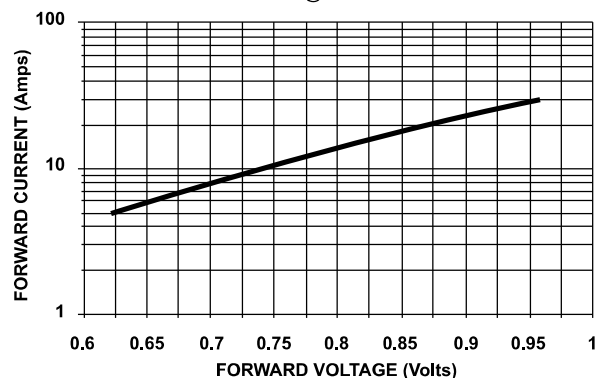
TYPICAL OPERATING CURVES
($T_A = 25^\circ C$ unless otherwise specified)



CASE OUTLINE: SED15HE100



TYPICAL FORWARD VOLTAGE
@ 25 $^\circ C$



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